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SSTUM32868

1.8 V 28-bit 1 : 2 configurable registered buffer with parity for DDR2-800 RDIMM applications

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Product data sheet

1. General description

The SSTUM32868 is a 1.8 V 28-bit 1 : 2 register specifically designed for use on two rank by four ($2R \times 4$) and similar high-density Double Data Rate 2 (DDR2) memory modules. It is similar in function to the JEDEC-standard 14-bit DDR2 register, but integrates the functionality of the normally required two registers in a single package, thereby freeing up board real-estate and facilitating routing to accommodate high-density Dual In-line Memory Module (DIMM) designs.

The SSTUM32868 also integrates a parity function, which accepts a parity bit from the memory controller, compares it with the data received on the D-inputs and indicates whether a parity error has occurred on its open-drain PTYERR pin (active LOW).

It further offers added features over the JEDEC standard register in that it is permanently configured for high output drive strength. This allows use in high density designs with heavier than normal net loading conditions. Furthermore, the SSTUM32868 features two additional chip select inputs, which allow more versatile enabling and disabling in densely populated memory modules. Both added features (drive strength and chip selects) are fully backward compatible to the JEDEC standard register. Finally, the SSTUM32868 is optimized for the fastest propagation delay in the SSTU family of registers.

The SSTUM32868 is packaged in a 176-ball, 8×22 grid, 0.65 mm ball pitch, thin profile fine-pitch ball grid array (TFBGA) package, which (while requiring a minimum 6 mm \times 15 mm of board space) allows for adequate signal routing and escape using conventional card technology.

2. Features

- 28-bit data register supporting DDR2
- Fully compliant to JEDEC standard for SSTUB32868
- Supports 2 rank by 4 DIMM density by integrating equivalent functionality of two JEDEC-standard DDR2 registers (that is, 2 × SSTUA32864 or 2 × SSTUA32866)
- Parity checking function across 22 input data bits
- Parity out signal
- Controlled multi-impedance output impedance drivers enable optimal signal integrity and speed
- Meets or exceeds SSTUB32868 JEDEC standard speed performance
- Supports up to 450 MHz clock frequency of operation
- Permanently configured for high output drive
- Optimized pinout for high-density DDR2 module design
- Chip-selects minimize power consumption by gating data outputs from changing state



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- Two additional chip select inputs allow optional flexible enabling and disabling
- Supports Stub Series Terminated Logic SSTL 18 data inputs
- Differential clock (CK and CK) inputs
- Supports Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) switching levels on the control and RESET inputs
- Single 1.8 V supply operation (1.7 V to 2.0 V)
- Available in 176-ball 6 mm × 15 mm, 0.65 mm ball pitch TFBGA package

3. Applications

- 400 MT/s to 800 MT/s high-density (for example, 2 rank by 4) DDR2 registered DIMMs
- DDR2 Registered DIMMs (RDIMM) desiring parity checking functionality

4. Ordering information

Table 1. Ordering information

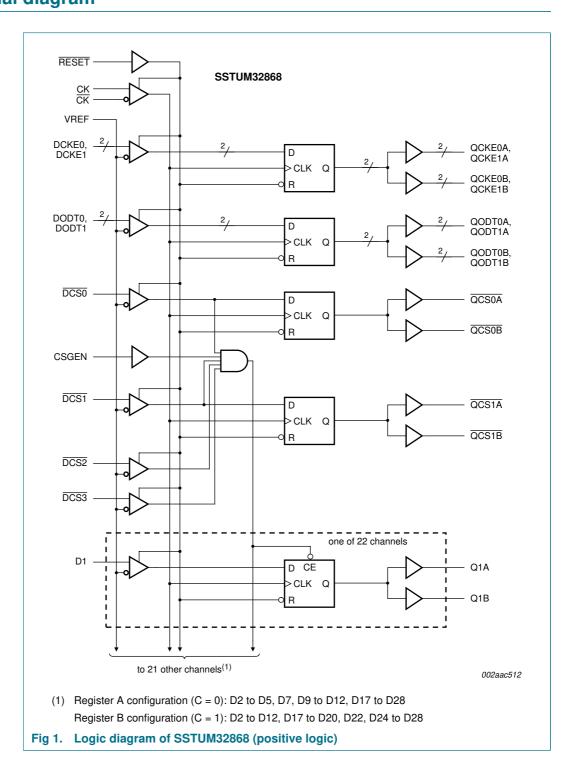
Type number	Solder process	Package						
		Name	Description	Version				
SSTUM32868ET/G	Pb-free (SnAgCu solder ball compound)	TFBGA176	plastic thin fine-pitch ball grid array package; 176 balls; body $6 \times 15 \times 0.7$ mm	SOT932-1				
SSTUM32868ET/S	Pb-free (SnAgCu solder ball compound)	TFBGA176	plastic thin fine-pitch ball grid array package; 176 balls; body $6\times15\times0.7$ mm	SOT932-1				

4.1 Ordering options

Table 2. Ordering options

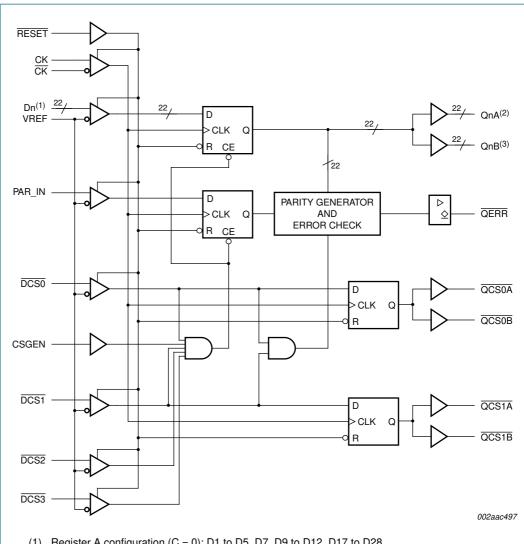
Type number	Temperature range
SSTUM32868ET/G	$T_{amb} = 0 ^{\circ}C to + 70 ^{\circ}C$
SSTUM32868ET/S	$T_{amb} = 0 ^{\circ}C \text{ to } +85 ^{\circ}C$

5. Functional diagram



SSTUM32868

1.8 V DDR2-800 configurable registered buffer with parity



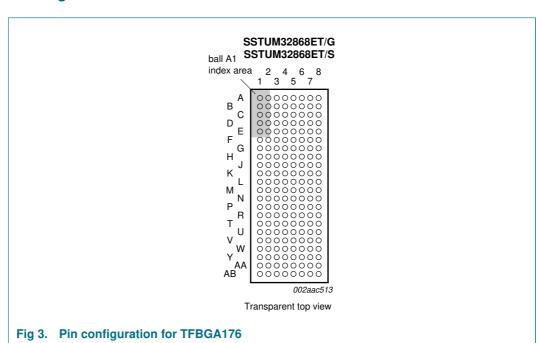
- (1) Register A configuration (C = 0): D1 to D5, D7, D9 to D12, D17 to D28

 Register B configuration (C = 1): D1 to D12, D17 to D20, D22, D24 to D28
- (2) Register A configuration (C = 0): Q1A to Q5A, Q7A, Q9A to Q12A, Q17A to Q28A Register B configuration (C = 1): Q1A to Q12A, Q17A to Q20A, Q22A, Q24A to Q28A
- (3) Register A configuration (C = 0): Q1B to Q5B, Q7B, Q9B to Q12B, Q17B to Q28B Register B configuration (C = 1): Q1B to Q12B, Q17B to Q20B, Q22B, Q24B to Q28B

Fig 2. Parity logic diagram (positive logic)

6. Pinning information

6.1 Pinning



	1	2	3	4	5	6	7	8
Α	D2	D1	С	GND	VREF	GND	Q1A	Q1B
В	D4	D3	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q2A	Q2B
С	D6 (DCKE1)	D5	GND	GND	GND	GND	Q3A	Q3B
D	D8 (DCKE0)	D7	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q4A	Q4B
E	D9	Q6A (QCKE1A)	GND	GND	GND	GND	Q5A	Q5B
F	D10	Q8A (QCKE0A)	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q7A	Q6B (QCKE1B)
G	D11	Q10A	GND	GND	GND	GND	Q9A	Q7B
Н	D12	Q12A	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q11A	Q8B (QCKE0B)
J	DCS1 (D13)	QCS1A (Q13A)	GND	GND	GND	GND	Q10B	Q9B
К	DCS0 (D14)	QCS0A (Q14A)	DCS2	V _{DD}	V _{DD}	V _{DD}	Q12B	Q11B
L	CK	CSGEN	PAR_IN	GND	GND	GND	Q14B (QCS0B)	Q13B (QCS1B)
М	CK	RESET	QERR	V _{DD}	V _{DD}	V _{DD}	Q15B (QODT0B)	Q16B (QODT1B)
N	D15 (DODT0)	Q15A (QODT0A)	GND	GND	GND	GND	Q17B	Q18B
Р	D16 (DODT1)	Q16A (QODT1A)	DCS3	V _{DD}	V _{DD}	V _{DD}	Q19B	Q20B
R	D17	Q17A	GND	GND	GND	GND	Q18A	Q21B
Т	D18	Q19A	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q20A	Q22B
U	D19	Q21A	GND	GND	GND	GND	Q22A	Q23B
V	D20	Q23A	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q24A	Q24B
W	D21	D22	GND	GND	GND	GND	Q25A	Q25B
Υ	D23	D24	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q26A	Q26B
AA	D25	D26	GND	GND	GND	GND	Q27A	Q27B
AB	D27	D28	n.c.	V _{DD}	VREF	V _{DD}	Q28A	Q28B
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176-ball, 8×22 grid; top view.

Fig 4. Ball mapping (1 : 2 Register A; C = 0)

	1	2	3	4	5	6	7	8
Α	D2	D1	С	GND	VREF	GND	Q1A	Q1B
В	D4	D3	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q2A	Q2B
С	D6	D5	GND	GND	GND	GND	Q3A	Q3B
D	D8	D7	V _{DD}	V _{DD}	V _{DD}	V _{DD}	Q4A	Q4B
E	D9	Q6A	GND	GND	GND	GND	Q5A	Q5B
F	D10	Q8A	V _{DD}	V _{DD}	V _{DD}	V _{DD}	Q7A	Q6B
G	D11	Q10A	GND	GND	GND	GND	Q9A	Q7B
Н	D12	Q12A	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q11A	Q8B
J	D13 (DODT1)	Q13A (QODT1A)	GND	GND	GND	GND	Q10B	Q9B
К	D14 (DODT0)	Q14A (QODT0A)	DCS2	V _{DD}	V _{DD}	V _{DD}	Q12B	Q11B
L	СК	CSGEN	PAR_IN	GND	GND	GND	Q14B (QODT0B)	Q13B (QODT1B)
М	CK	RESET	QERR	V _{DD}	V _{DD}	V _{DD}	Q15B (QCS0B)	Q16B (QCS1B)
N	D15 (DCS0)	Q15A (QCS0A)	GND	GND	GND	GND	Q17B	Q18B
Р	D16 (DCS1)	Q16A (QCS1A)	DCS3	V _{DD}	V _{DD}	V _{DD}	Q19B	Q20B
R	D17	Q17A	GND	GND	GND	GND	Q18A	Q21B (QCKE0B)
Т	D18	Q19A	V_{DD}	V _{DD}	V _{DD}	V _{DD}	Q20A	Q22B
U	D19	Q21A (QCKE0A)	GND	GND	GND	GND	Q22A	Q23B (QCKE1B)
V	D20	Q23A (QCKE1A)	V _{DD}	V _{DD}	V _{DD}	V _{DD}	Q24A	Q24B
W	D21 (DCKE0)	D22	GND	GND	GND	GND	Q25A	Q25B
Υ	D23 (DCKE1)	D24	V _{DD}	V _{DD}	V _{DD}	V _{DD}	Q26A	Q26B
AA	D25	D26	GND	GND	GND	GND	Q27A	Q27B
AB	D27	D28	n.c.	V _{DD}	VREF	V _{DD}	Q28A	Q28B
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176-ball, 8×22 grid; top view.

Fig 5. Ball mapping (1 : 2 Register B; C = 1)

6.2 Pin description

Table 3. Pin description

Table 3.	Pin description					
Symbol	Pin		Туре	Description		
	1 : 2 Register A (C = 0)	1 : 2 Register B (C = 1)				
Ungated	inputs					
DCKE0	D1	W1	SSTL_18	The outputs of this register will not be		
DCKE1	C1	Y1		suspended by the $\overline{DCS0}$ and $\overline{DCS1}$ control.		
DODT0	N1	K1	SSTL_18	The outputs of this register will not be		
DODT1	P1	J1		suspended by the $\overline{DCS0}$ and $\overline{DCS1}$ control.		
Chip Sele	ect gated inputs					
D1 to D28	A2, A1, B2, B1, C2, C1, D2, D1, E1, F1, G1, H1, N1, P1, R1, T1, U1, V1, W1, W2, Y1, Y2, AA1, AA2, AB1, AB2	A2, A1, B2, B1, C2, C1, D2, D1, E1, F1, G1, H1, J1, K1, N1, P1, R1, T1, U1, V1, W1, W2, Y1, Y2, AA1, AA2, AB1, AB2	SSTL_18	Data inputs, clocked in on the crossing of the rising edge of CD and the falling edge of CK.		
Chip Sele	ect inputs					
DCS0	K1	N1	SSTL_18	Chip select inputs. These pins initiate		
DCS1	J1	P1		DRAM address/command decodes, and as such at least one will be LOW when a		
DCS2	K3	K3		valid address/command is present. The		
DCS3	P3	P3		register can be programmed to re-drivall D-inputs (CSGEN = HIGH) only what least one chip select input is LOW. CSGEN, DCSO and DCS1 inputs are HIGH, D1 to D28[1] inputs will be disabled.		
Configur	ation control inputs					
С	A3	A3	LVCMOS input	Configuration control inputs; Register A or Register B		
Re-driver	n outputs					
Q1A to Q28A	A7, B7, C7, D7, E7, E2, F7, F2, G7, G2, H7, H2, N2, P2, R2, R7, T2, T7, U2, U7, V2, V7, W7, Y7, AA7, AB7	A7, B7, C7, D7, E7, E2, F7, F2, G7, G2, H7, H2, J2, K2, N2, P2, R2, R7, T2, T7, U2, U7, V2, V7, W7, Y7, AA7, AB7	1.8 V CMOS outputs	Data outputs[2] that are suspended by the DCS0 and DCS1 control.		
Q1B to Q28B	A8, B8, C8, D8, E8, F8, G8, H8, J8, J7, K8, K7, L8, L7, M7, M8, N7, N8, P7, P8, R8, T8, V8, U8, W8, Y8, AA8, AB8	A8, B8, C8, D8, E8, F8, G8, H8, J8, J7, K8, K7, L8, L7, M7, M8, N7, N8, P7, P8, R8, T8, U8, V8, W8, Y8, AA8, AB8				
QCS0A	K2	N2	1.8 V	Data outputs that will not be suspended		
QCS0B	L7	M7	CMOS	by the $\overline{DCS0}$ and $\overline{DCS1}$ control.		
QCS1A	J2	P2	outputs			
QCS1B	L8	M8				



Table 3. Pin description ... continued

				December 1				
Symbol	Pin		Туре	Description				
	1 : 2 Register A (C = 0)	1 : 2 Register B (C = 1)						
QCKE0A	F2	U2	1.8 V	Data outputs that will not be suspended				
QCKE0B	H8	R8	CMOS outputs	by the $\overline{DCS0}$ and $\overline{DCS1}$ control.				
QCKE1A	E2	V2						
QCKE1B	F8	U8						
QODT0A	N2	K2	1.8 V	Data outputs that will not be suspended				
QODT0B	M7	L7	CMOS outputs	by the $\overline{DCS0}$ and $\overline{DCS1}$ control.				
QODT1A	P2	J2						
QODT1B	M8	L8						
Output er	ror							
QERR	M3	M3	open-drain output	Output error bit; generated on clock cycle after the corresponding data output.				
Parity inp	ut							
PAR_IN	L3	L3	SSTL_18	Parity input. Arrives one clock cycle after the corresponding data input.				
Program	inputs							
CSGEN	L2	L2	LVCMOS input	Chip select gate enable. When HIGH, the D1 to D28[1] inputs will be latched only when at least one chip select input is LOW during the rising edge of the clock. When LOW, the D1 to D28[1] inputs will be latched and re-driven on every rising edge of the clock.				
Clock inp	uts							
CK	L1	L1	differential input	Positive master clock input.				
CK	M1	M1	differential input	Negative master clock input.				
Miscellan	eous inputs							
RESET	M2	M2	LVCMOS input	Asynchronous reset input. Resets registers and disables VREF data and clock differential-input receivers.				

 Table 3.
 Pin description ...continued

Symbol	Pin		Туре	Description	
	1 : 2 Register A (C = 0)	1 : 2 Register B (C = 1)			
VREF	A5, AB5	A5, AB5	0.9 V nominal	Input reference voltage.	
V_{DD}	D5, D6, F3, F4, F5, F6, H3, H4, H5, H6, K4, K5, K6, M4, M5, M6, P4, P5, P6, T3, T4, T5, T6, V3, V4, V5,	H4, H5, H6, K4, K5, K6, M4, M5, M6, P4, P5, P6,	1.8 V nominal	Power supply voltage.	
GND	E3, E4, E5, E6, G3, G4, G5, G6, J3, J4, J5, J6, L4, L5, L6, N3, N4, N5, N6, R3, R4, R5, R6, U3, U4, U5,	G5, G6, J3, J4, J5, J6, L4, L5, L6, N3, N4, N5, N6, R3,	ground input	Ground.	

^[1] Data inputs = D1 to D5, D7, D9 to D12, D17 to D28 when C = 0. Data inputs = D1 to D12, D17 to D20, D22, D24 to D28 when C = 1.

7. Functional description

7.1 Function table

Table 4. Function table (each flip-flop)

			Inputs					Out	tputs <mark>[1]</mark>	
RESET	DCS0[2]	DCS1[2]	CSGEN	СК	CK	Dn, DODTn, DCKEn	Qn	QCS0x	QCS1x	QODTn, QCKEn
Н	L	L	X	\uparrow	\downarrow	L	L	L	L	L
Н	L	L	X	\uparrow	\downarrow	Н	Н	L	L	Н
Н	L	L	X	L or H	L or H	X	Q_0	Q_0	Q_0	Q_0
Н	L	Н	X	↑	\downarrow	L	L	L	Н	L
Н	L	Н	X	↑	\downarrow	Н	Н	L	Н	Н
Н	L	Н	X	L or H	L or H	X	Q_0	Q_0	Q_0	Q_0
Н	Н	L	X	↑	\downarrow	L	L	Н	L	L
Н	Н	L	X	↑	\downarrow	Н	Н	Н	L	Н
Н	Н	L	X	L or H	L or H	X	Q_0	Q_0	Q_0	Q_0
Н	Н	Н	L	↑	\downarrow	L	L	Н	Н	L
Н	Н	Н	L	↑	\downarrow	Н	Н	Н	Н	Н
Н	Н	Н	L	L or H	L or H	Χ	Q_0	Q_0	Q_0	Q_0
Н	Н	Н	Н	↑	\downarrow	L	Q_0	Н	Н	L

^[2] Data outputs = Q1x to Q5x, Q7x, Q9x to Q12x, Q17x to Q28x when C = 0. Data outputs = Q1x to Q12x, Q17x to Q20x, Q22x, Q24x to Q28x when C = 1.

Table 4. Function table (each flip-flop) ...continued

			Inputs				Outputs[1]			
RESET	DCS0[2]	DCS1[2]	CSGEN	CK	CK	Dn, DODTn, DCKEn	Qn	QCS0x	QCS1x	QODTn, QCKEn
Н	Н	Н	Н	↑	\downarrow	Н	Q_0	Н	Н	Н
Н	Н	Н	Н	L or H	L or H	X	Q_0	Q_0	Q_0	Q_0
L	X or floating	L	L	L	L					

^[1] Q_0 is the previous state of the associated output.

Table 5. Parity and standby function table

			Inputs				Output
RESET	DCS0[1]	DCS1 ^[1]	CK	CK	Σ of inputs = H (D1 to D28)	PAR_IN[2]	QERR[3][4]
Н	L	Χ	^	\	even	L	Н
Н	L	Χ	1	\downarrow	odd	L	L
Н	L	Χ	↑	\downarrow	even	Н	L
Н	L	Χ	↑	\downarrow	odd	Н	Н
Н	Χ	L	1	\downarrow	even	L	Н
Н	Χ	L	1	\downarrow	odd	L	L
Н	Χ	L	1	\downarrow	even	Н	L
Н	Χ	L	↑	\downarrow	odd	Н	Н
Н	Н	Н	1	\downarrow	Χ	Х	QERR ₀ ^[5]
Н	Χ	Χ	L or H	L or H	Χ	Χ	QERR ₀
L	X or floating	X or floating	X or floating	X or floating	Χ	X or floating	Н

^[1] $\overline{DCS2}$ and $\overline{DCS3}$ operate identically to $\overline{DCS0}$ and $\overline{DCS1}$ with regard to the parity function.

7.2 Functional information

The SSTUM32868 is a 28-bit 1 : 2 configurable registered buffer designed for 1.7 V to 1.9 V V_{DD} operation.

All inputs are compatible with the JEDEC standard for SSTL_18, except the chip-select gate-enable (CSGEN), control (C), and reset (RESET) inputs, which are LVCMOS. All outputs are edge-controlled circuits optimized for unterminated DIMM loads, and meet SSTL_18 specifications, except the open-drain error (QERR) output.

 $[\]overline{DCS2}$ and $\overline{DCS3}$ operate identically to $\overline{DCS0}$ and $\overline{DCS1}$, except they do not have corresponding re-driven (QCS) outputs.

^[2] PAR_IN arrives one clock cycle after the data to which it applies.

^[3] This transition assumes QERR is HIGH at the crossing of CK going HIGH and CK going LOW. If QERR is LOW, it stays latched LOW for two clock cycles or until RESET is driven LOW.

^[4] $\overline{\text{QERR}}_0$ is the previous state of output $\overline{\text{QERR}}$.

^[5] If \overline{DCSO} , $\overline{DCS1}$, $\overline{DCS2}$, $\overline{DCS3}$ and CSGEN are driven HIGH, the device is placed in Low-Power Mode (LPM). If a parity error occurs on the clock cycle before the device enters the LPM and the \overline{QERR} output is driven LOW, it stays latched LOW for the LPM duration plus two clock cycles or until \overline{RESET} is driven LOW.

The device supports low-power standby operation. When RESET is LOW, the differential input receivers are disabled, and undriven (floating) data, clock, and reference voltage (VREF) inputs are allowed. In addition, when RESET is LOW, all registers are reset and all outputs are forced LOW except QERR. The LVCMOS RESET and C inputs always must be held at a valid logic HIGH or LOW level.

To ensure defined outputs from the register before a stable clock has been supplied, RESET must be held in the LOW state during power-up.

In the DDR2 RDIMM application, $\overline{\text{RESET}}$ is specified to be completely asynchronous with respect to CK and $\overline{\text{CK}}$. Therefore, no timing relationship can be ensured between the two. When entering reset, the register will be cleared and the data outputs will be driven LOW quickly, relative to the time to disable the differential input receivers. However, when coming out of reset, the register will become active quickly, relative to the time to enable the differential input receivers. As long as the data inputs are LOW, and the clock is stable during the time from the LOW-to-HIGH transition of $\overline{\text{RESET}}$ until the input receivers are fully enabled, the design of the SSTUM32868 must ensure that the outputs will remain LOW, thus ensuring no glitches on the output.

The SSTUM32868 includes a parity checking function. Parity, which arrives one cycle after the data input to which it applies, is checked on the PAR_IN input of the device. The corresponding $\overline{\text{QERR}}$ output signal for the data inputs is generated two clock cycles after the data, to which the $\overline{\text{QERR}}$ signal applies, is registered.

The SSTUM32868 accepts a parity bit from the memory controller on the parity bit (PAR_IN) input, compares it with the data received on the DIMM-independent D inputs (D1 to D5, D7, D9 to D12, D17 to D28 when C = 0; or D1 to D12, D17 to D20, D22, D24 to D28 when C = 1) and indicates whether a parity error has occurred on the open-drain $\overline{\text{QERR}}$ pin (active LOW). The convention is even parity, that is, valid parity is defined as an even number of ones across the DIMM-independent data inputs combined with the parity input bit. To calculate parity, all DIMM-independent D inputs must be tied to a known logic state.

If an error occurs and the $\overline{\text{QERR}}$ output is driven LOW, it stays latched LOW for a minimum of two clock cycles or until $\overline{\text{RESET}}$ is driven LOW. If two or more consecutive parity errors occur, the $\overline{\text{QERR}}$ output is driven LOW and latched LOW for a clock duration equal to the parity error duration or until $\overline{\text{RESET}}$ is driven LOW. If a parity error occurs on the clock cycle before the device enters the Low-Power Mode (LPM) and the $\overline{\text{QERR}}$ output is driven LOW, then it stays latched LOW for the LPM duration plus two clock cycles or until $\overline{\text{RESET}}$ is driven LOW. The DIMM-dependent signals (DCKE0, DCKE1, DODT0, DODT1, $\overline{\text{DCS0}}$, $\overline{\text{DCS1}}$, $\overline{\text{DCS2}}$ and $\overline{\text{DCS3}}$) are not included in the parity check computation.

The C input controls the pinout configuration from Register A configuration (when LOW) to Register B configuration (when HIGH). The C input should not be switched during normal operation. It should be hard-wired to a valid LOW or HIGH level to configure the register in the desired mode.

The device also supports low-power active operation by monitoring both system chip select ($\overline{DCS0}$, $\overline{DCS1}$, $\overline{DCS2}$ and $\overline{DCS3}$) and CSGEN inputs and will gate the Qn outputs from changing states when CSGEN, $\overline{DCS0}$ and $\overline{DCS1}$ inputs are HIGH. If CSGEN or the \overline{DCSn} inputs are LOW, the Qn outputs will function normally. Also, if all \overline{DCSn} inputs are HIGH, the device will gate the \overline{QERR} output from changing states. If any of the \overline{DCSn} are

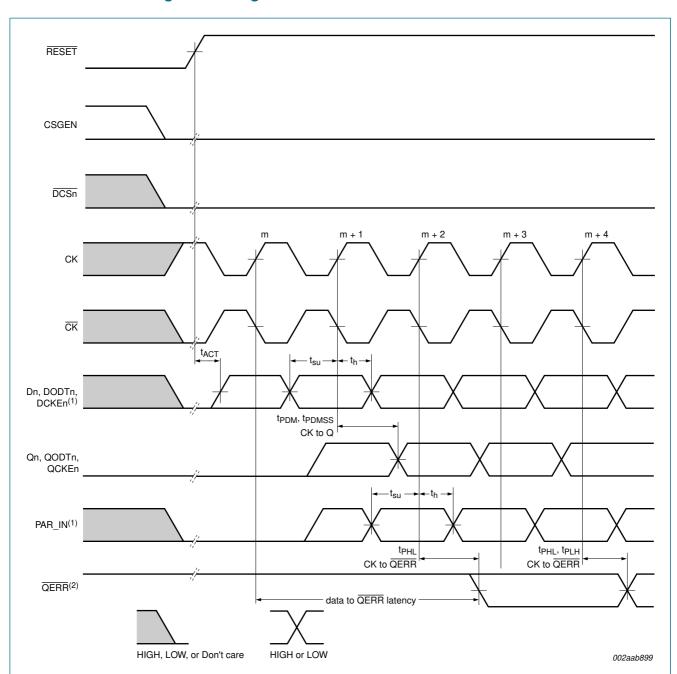


LOW, the $\overline{\text{QERR}}$ output will function normally. The $\overline{\text{RESET}}$ input has priority over the $\overline{\text{DCSn}}$ control, and when driven LOW will force the Qn outputs LOW and the $\overline{\text{QERR}}$ output HIGH. If the chip-select control functionality is not desired, then the CSGEN input can be hard-wired to ground (GND), in which case the set-up time requirement for $\overline{\text{DCSn}}$ would be the same as for the other D data inputs. To control the Low-power mode with $\overline{\text{DCSn}}$ only, the CSGEN input should be pulled up to V_{DD} through a pull-up resistor.

The two VREF pins (A5 and AB5) are connected together internally by approximately 150 Ω . However, it is necessary to connect only one of the two VREF pins to the external V_{ref} power supply. An unused VREF pin should be terminated with a V_{ref} coupling capacitor.

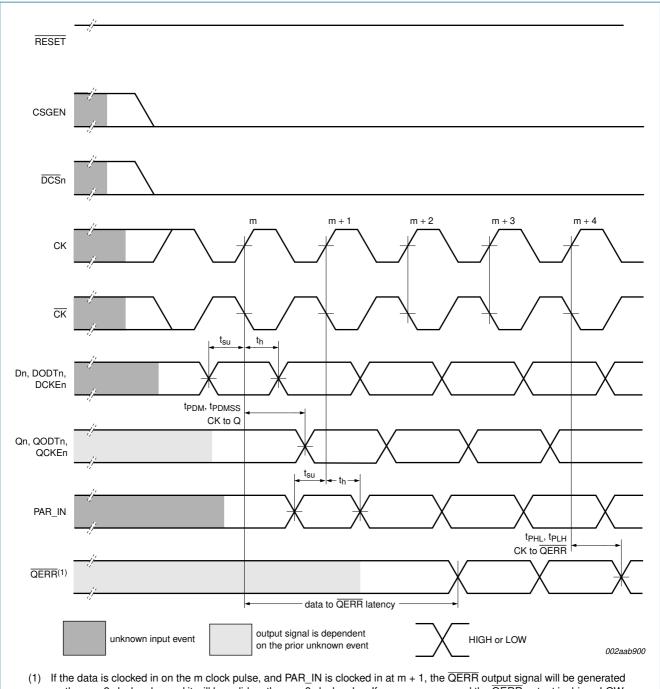
The SSTUM32868 is available in a TFGBA176 package.

7.3 Register timing



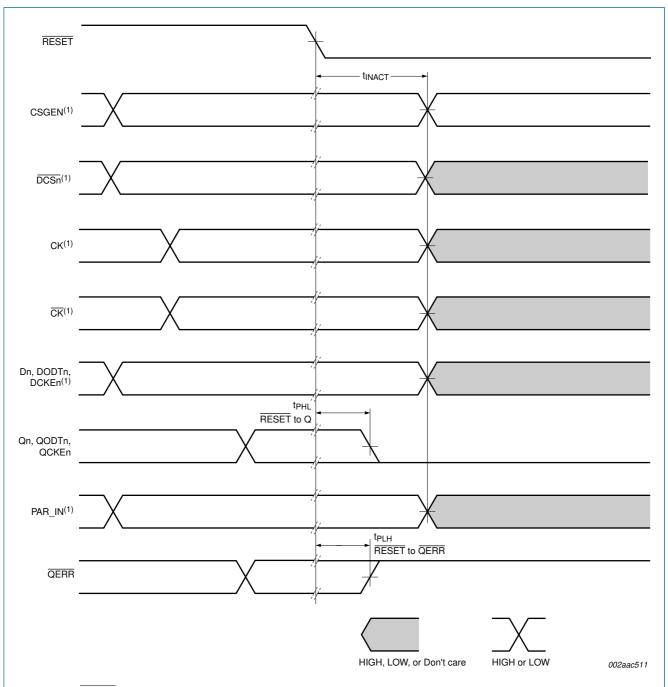
- (1) After $\overline{\text{RESET}}$ is switched from LOW to HIGH, all data and PAR_IN input signals must be set and held LOW for a minimum time of $t_{\text{ACT(max)}}$ to avoid false error.
- (2) If the data is clocked on the m clock pulse, and PAR_IN is clocked in at m + 1, the QERR output signal will be produced on the m + 2 clock pulse and it will be valid on the m + 3 clock pulse.

Fig 6. Timing diagram during start-up (RESET switches from LOW to HIGH)



(1) If the data is clocked in on the m clock pulse, and PAR_IN is clocked in at m + 1, the QERR output signal will be generated on the m + 2 clock pulse and it will be valid on the m + 3 clock pulse. If an error occurs and the QERR output is driven LOW, it stays LOW for a minimum of two clock cycles or until RESET is driven LOW.

Fig 7. Timing diagram during normal operation (RESET = HIGH)



(1) After RESET is switched from HIGH to LOW, all data and clock input signals must be held at valid logic levels (not floating) for a minimum time of t_{INACT(max)}.

Fig 8. Timing diagram during shutdown (RESET switches from HIGH to LOW)

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	5 +2.5	V
VI	input voltage (receiver)		[1][2] -0.5	5 +2.5	V
Vo	output voltage (driver)		[1][2] -0.5	$V_{DD} + 0$.5 V
I _{IK}	input clamping current	$V_I < 0 \text{ V or } V_I > V_{DD}$	-	±50	mA
I _{OK}	output clamping current	$V_O < 0 \text{ V or } V_O > V_{DD}$	-	±50	mA
I _O	output current (continuous)	$0 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{DD}}$	-	±50	mA
Iccc	continuous current through each V_{DD} or GND pin		-	±100	mA
T _{stg}	storage temperature		-65	+150	°C
V _{esd}	electrostatic discharge	Human Body Model (HBM); 1.5 k Ω ; 100 pF	2	-	kV
	voltage	Machine Model (MM); 0 Ω; 200 pF	200	-	V

^[1] The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DD}	supply voltage			1.7	-	2.0	V
V_{ref}	reference voltage			$0.49 \times V_{DD}$	$0.50 \times V_{DD}$	$0.51\times V_{DD}$	V
V_{T}	termination voltage			$V_{ref} - 0.040$	V_{ref}	$V_{ref} + 0.040$	V
VI	input voltage			0	-	V_{DD}	V
V _{IH(AC)}	AC HIGH-level input voltage	Dn, CSR and PAR_IN inputs	[1]	$V_{ref} + 0.250$	-	-	V
V _{IL(AC)}	AC LOW-level input voltage	Dn, CSR and PAR_IN inputs	[1]	-	-	$V_{ref} - 0.250$	V
V _{IH(DC)}	DC HIGH-level input voltage	Dn, $\overline{\text{CSR}}$ and PAR_IN inputs	[1]	$V_{ref} + 0.125$	-	-	V
$V_{IL(DC)}$	DC LOW-level input voltage	Dn, $\overline{\text{CSR}}$ and PAR_IN inputs	[1]	-	-	$V_{ref} - 0.125$	V
V_{IH}	HIGH-level input voltage	RESET, CSGEN	[2]	$0.65 \times V_{DD}$	-	-	V
V _{IL}	LOW-level input voltage	RESET, CSGEN	[2]	-	-	$0.35 \times V_{DD}$	V
V_{ICR}	common mode input voltage range	CK, CK		0.675	-	1.125	V
V_{ID}	differential input voltage	CK, CK		600	-	-	mV
I _{OH}	HIGH-level output current			-	-	-8	mA
I _{OL}	LOW-level output current			-	-	8	mΑ
T _{amb}	ambient temperature	operating in free air					
		SSTUM32868ET/G		0	-	+70	°C
		SSTUM32868ET/S		0	-	+85	°C

^[1] The differential inputs must not be floating, unless $\overline{\text{RESET}}$ is LOW.

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^[2] This value is limited to 2.5 V maximum.

^[2] The RESET input of the device must be held at valid logic levels (not floating) to ensure proper device operation.

10. Characteristics

Table 8. Characteristics

Over recommended operating conditions, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	$I_{OH} = -6 \text{ mA}; V_{DD} = 1.7 \text{ V}$	1.2	-	-	٧
V _{OL}	LOW-level output voltage	$I_{OL} = 6 \text{ mA}; V_{DD} = 1.7 \text{ V}$	-	-	0.5	V
lı	input current	all inputs; $V_I = V_{DD}$ or GND; $V_{DD} = 1.9 \text{ V}$	-	-	±5	μΑ
I _{DD}	supply current	static standby; $\overline{RESET} = GND$; $V_{DD} = 1.9 V$; $I_O = 0 \text{ mA}$	-	-	2	mA
		static operating; $\overline{RESET} = V_{DD}$; $V_{DD} = 1.9 \text{ V}$; $I_O = 0 \text{ mA}$; $V_I = V_{IH(AC)} \text{ or } V_{IL(AC)}$	-	-	80	mA
I _{DDD}	dynamic operating current per MHz	clock only; $\overline{\text{RESET}} = \text{V}_{\text{DD}}$; $\text{V}_{\text{I}} = \text{V}_{\text{IH}(AC)}$ or $\text{V}_{\text{IL}(AC)}$; CK and $\overline{\text{CK}}$ switching at 50 % duty cycle. $\text{I}_{\text{O}} = 0$ mA; $\text{V}_{\text{DD}} = 1.8$ V	-	16	-	μА
		per each data input (1 : 1 mode); RESET = V_{DD} ; $V_I = V_{IH(AC)}$ or $V_{IL(AC)}$; CK and \overline{CK} switching at 50 % duty cycle. One data input switching at half clock frequency, 50 % duty cycle. $I_O = 0$ mA; $V_{DD} = 1.8$ V	-	19	-	μА
		per each data input (1 : 2 mode); $\overline{RESET} = V_{DD}; \ V_I = V_{IH(AC)} \ or \ V_{IL(AC)};$ CK and \overline{CK} switching at 50 % duty cycle. One data input switching at half clock frequency, 50 % duty cycle. $I_O = 0 \ mA;$ $V_{DD} = 1.8 \ V$	-	19	-	μΑ
C _i	input capacitance	Dn, CSGEN, PAR_IN inputs; $V_I = V_{ref} \pm 250 \text{ mV}; V_{DD} = 1.8 \text{ V}$	2.5	-	4	pF
		\overline{DCSn} ; V_{ICR} = 0.9 V; V_{ID} = 600 mV; V_{DD} = 1.8 V	2.5	-	4	pF
		CK and \overline{CK} ; V_{ICR} = 0.9 V; V_{ID} = 600 mV; V_{DD} = 1.8 V	2	-	3	pF
		$\overline{\text{RESET}}$; $V_{\text{I}} = V_{\text{DD}}$ or GND; $V_{\text{DD}} = 1.8 \text{ V}$	3	-	5	pF
Z _o	output impedance	instantaneous	[1] -	7	-	Ω
		steady-state	-	53	-	Ω

^[1] Instantaneous is defined as within < 2 ns following the output data transition edge.

Table 9. Timing requirements

Over recommended operating conditions, unless otherwise noted.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f _{clk}	clock frequency			-	-	450	MHz
t_W	pulse duration	CK, CK HIGH or LOW		1	-	-	ns
t _{ACT}	differential inputs active time		[1][2]	-	-	10	ns
t _{INACT}	differential inputs inactive time		[1][3]	-	-	15	ns
t _{su}	set-up time	$\overline{\text{DCSn}}$ before CK \uparrow , $\overline{\text{CK}}\downarrow$, $\overline{\text{CSR}}$ HIGH; $\overline{\text{CSR}}$ before CK \uparrow , $\overline{\text{CK}}\downarrow$, $\overline{\text{DCSn}}$ HIGH		0.6	-	-	ns
		$\overline{\text{DCSn}}$ before CK \uparrow , $\overline{\text{CK}}\downarrow$, $\overline{\text{CSR}}$ LOW		0.5	-	-	ns
		DODTn, DCKEn ad Dn before CK \uparrow , $\overline{\text{CK}} \downarrow$		0.5	-	-	ns
		PAR_IN before CK↑, CK↓		0.5	-	-	ns
t _h	hold time	$\overline{\text{DCSn}}$, DODTn, DCKEn and Dn after CK \uparrow , $\overline{\text{CK}}\downarrow$		0.4	-	-	ns
		PAR_IN after CK↑, CK↓		0.4	-	-	ns

^[1] This parameter is not necessarily production tested.

Table 10. Switching characteristics

Over recommended operating conditions, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{clk(max)}	maximum clock frequency	input	450	-	-	MHz
t _{PDM}	peak propagation delay	single bit switching; from CK↑ and CK↓ to Qn	<u>U</u> 1.1	-	1.5	ns
t _{PLH}	LOW-to-HIGH propagation delay	from CK \uparrow and $\overline{\text{CK}}\downarrow$ to $\overline{\text{QERR}}$	1.2	-	3	ns
		from RESET↑ to QERR↓	-	-	3	ns
t _{PHL}	HIGH-to-LOW propagation delay	from CK $↑$ and $\overline{\text{CK}} ↓$ to $\overline{\text{QERR}}$	1	-	2.4	ns
		from RESET↑ to Qn↓	-	-	3	ns
t _{PDMSS}	simultaneous switching peak propagation delay	from CK↑ and CK↓ to Qn	<u>[1]</u> -	-	1.6	ns

^[1] Includes 350 ps of test-load transmission line delay.

Table 11. Output edge rates

Over recommended operating conditions, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV/dt_r	rising edge slew rate	from 20 % to 80 %	1	-	4	V/ns
dV/dt_f	falling edge slew rate	from 80 % to 20 %	1	-	4	V/ns
dV/dt_Δ	absolute difference between dV/dt_r and dV/dt_f	(from 20 % to 80 %) or (from 80 % to 20 %)	-	-	1	V/ns

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^[2] VREF must be held at a valid input voltage level, and data inputs must be held LOW for a minimum time of t_{ACT(max)} after RESET is taken HIGH.

^[3] VREF, data and clock inputs must be held at valid voltage levels (not floating) a minimum time of t_{INACT(max)} after RESET is taken LOW.

SSTUM32868

1.8 V DDR2-800 configurable registered buffer with parity

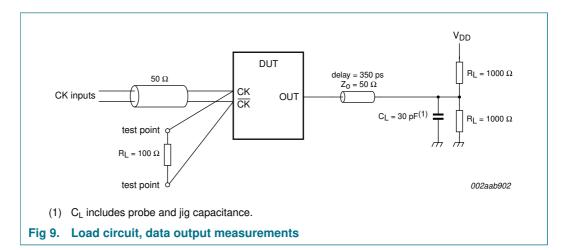
11. Test information

11.1 Parameter measurement information for data output load circuit

$$V_{DD} = 1.8 \ V \pm 0.1 \ V.$$

All input pulses are supplied by generators having the following characteristics: Pulse Repetition Rate (PRR) \leq 10 MHz; Z_0 = 50 $\Omega;$ input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.

The outputs are measured one at a time with one transition per measurement.



RESET 0.5V_{DD} V_{DD} $0.5V_{DD}$ $0.5V_{DD}$ 0.5V

input

V_{ICR}

V_{ICR}

V_{ID}

V_{IL}

002aaa373

V_{ID} = 600 mV.

V_{IH} = V_{ref} + 250 mV (AC voltage levels) for differential inputs. V_{IH} = V_{DD} for LVCMOS inputs.

V_{IL} = V_{ref} - 250 mV (AC voltage levels) for differential inputs. V_{IL} = GND for LVCMOS inputs.

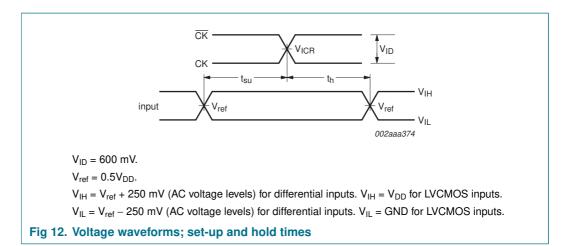
Fig 11. Voltage waveforms; pulse duration

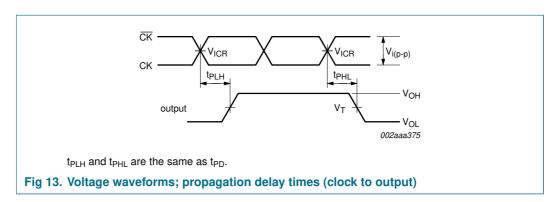
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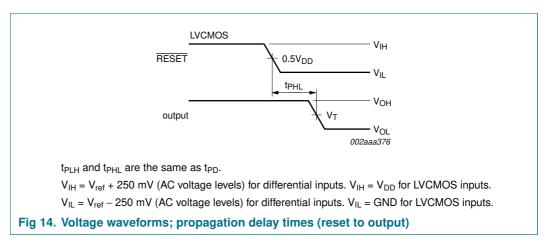
Fig 10. Voltage and current waveforms; inputs active and inactive times

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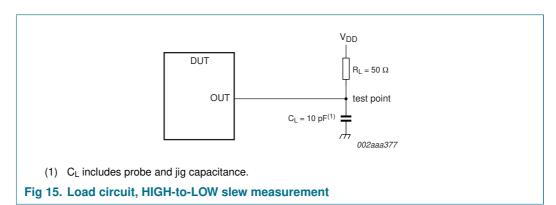
SSTUM32868

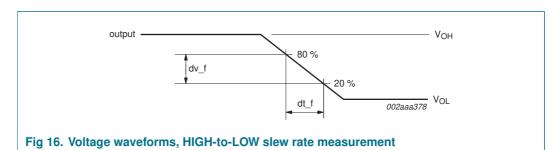
1.8 V DDR2-800 configurable registered buffer with parity

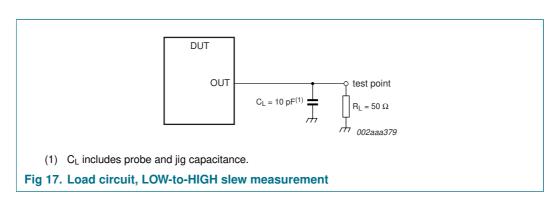
11.2 Data output slew rate measurement

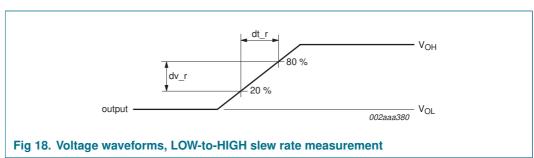
 $V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}.$

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; $Z_0 = 50~\Omega$; input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.





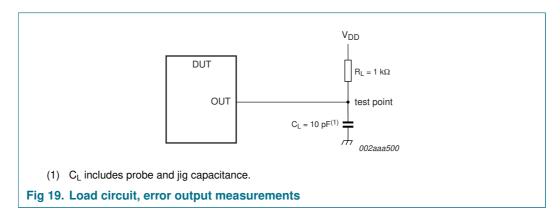




11.3 Error output load circuit and voltage measurement

 $V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}.$

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; $Z_0 = 50 \Omega$; input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.



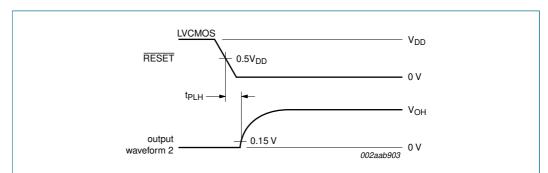


Fig 20. Voltage waveforms, open-drain output LOW-to-HIGH transition time with respect to $\overline{\text{RESET}}$ input

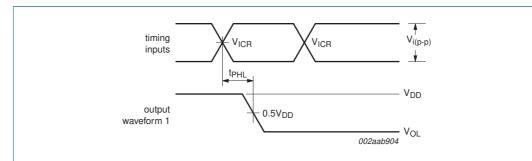


Fig 21. Voltage waveforms, open-drain output HIGH-to-LOW transition time with respect to clock inputs

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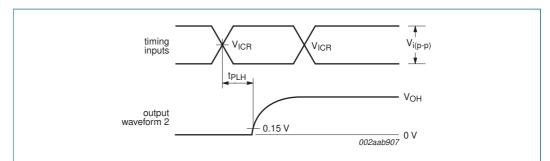


Fig 22. Voltage waveforms, open-drain output LOW-to-HIGH transition time with respect to clock inputs

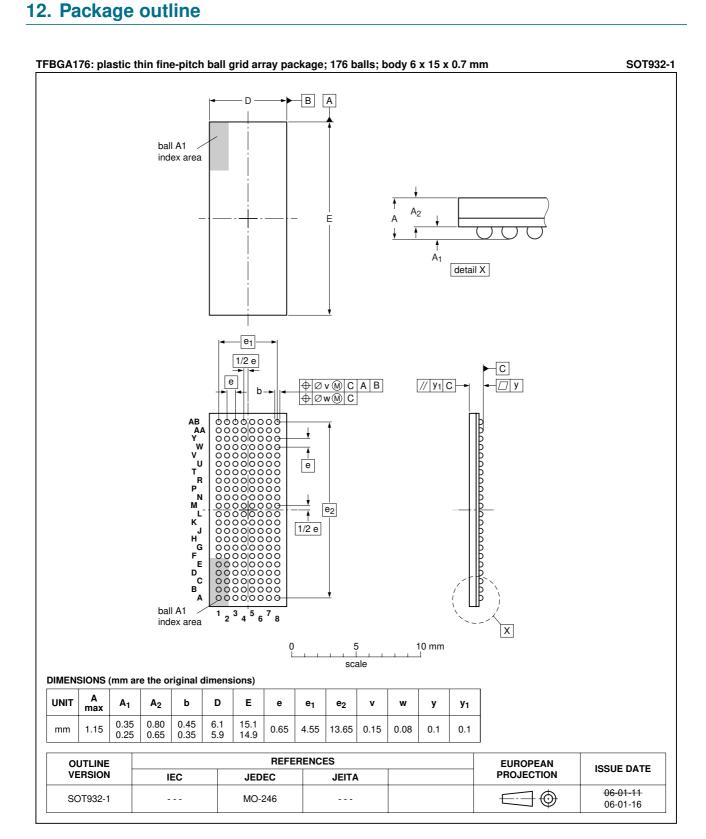


Fig 23. Package outline SOT932-1 (TFBGA176)

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